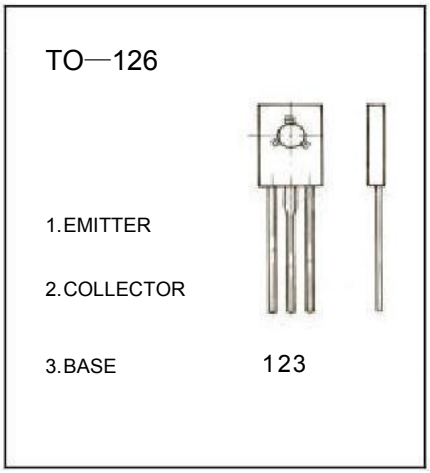
TO-126 Plastic-Encapsulate Transistors

BD435 TRANSISTOR（ NPN ）



FEATURES

Power dissipation

P_{CM}: 1.25 W（Tamb=25℃）

Collector current

I_{CM}: 4.0 A

Collector-base voltage

$V_{(BR)CBO}$: 32 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter sustaining voltage	V_{CEO}	I_C=100mA,I_E=0	32			V
Collector cut-off current	I_{CBO}	V_{CB}=32V,I_E=0			100	μA
Collector cut-off current	I_{CEO}	V_{CE}=32V,I_E=0			100	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			1	mA
DC current gain	$h_{FE(1)}$	V_{CE}=1V,I_C=500mA	85	140		
DC current gain	$h_{FE(2)}$	V_{CE}=5V,I_C=10mA	40	130		
DC current gain	$h_{FE(3)}$	V_{CE}=1V,I_C=2A	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=3A,I_B=0.3A		0.2	0.5	V
Base-emitter voltage	V_{BE}	V_{CE}=1V,I_C=2A			1.1	V
Transition frequency	f_T	V_{CE}=1V,I_C=250mA	3			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	1	2	3
Range	40-80	70-140	140-200